Alfa-MOS Technology

AFP7127S
30V P-Channel Enhancement Mode MOSFET

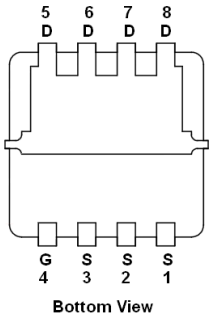
General Description

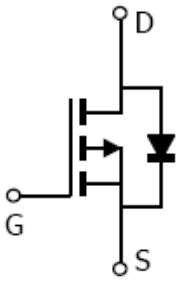
AFP7127S, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.
These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

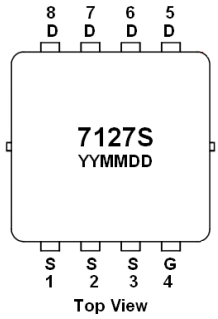
Features

- -30V/-10A,$R_{DS(ON)}$=17mΩ@V_{GS}=-10V
- -30V/-7A,$R_{DS(ON)}$=27mΩ@V_{GS}=-4.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN3.3X3.3-8L package design

Pin Description (DFN3.3X3.3-8L)







Application

- DC-DC Converter
- POL

Pin Define

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP7127SFN308RG	7127S	DFN3.3X3.3-8L	Tape & Reel	5000 EA

※ YY year code
※ MM month code
※ DD date code
※ AFP7127SFN308RG : 13”Tape & Reel ; Pb- Free ; Halogen- Free

Absolute Maximum Ratings

(T_A=25℃ Unless otherwise noted)

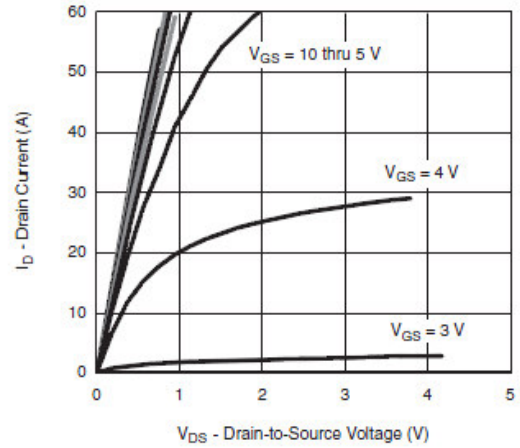
Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	-10	A
	T_A=70℃		-8	
Pulsed Drain Current		I_{DM}	-50	A
Continuous Source Current(Diode Conduction)	T_C=25℃	I_S	-16	A
Power Dissipation	T_A=25℃	P_D	3.8	W
	T_A=70℃		2	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	120	℃/W

Electrical Characteristics

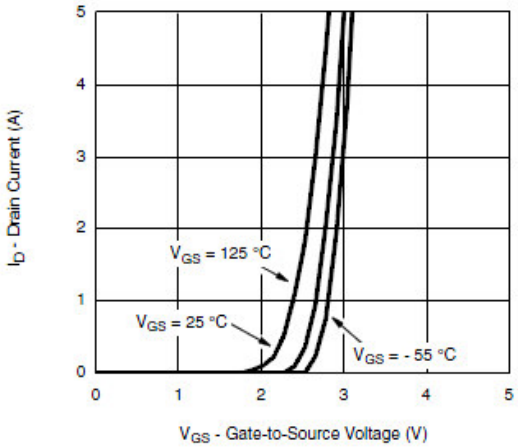
(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-1.0		-2.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±25V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V			-1	uA
		V_{DS}=-24V,V_{GS}=0V T_J=85℃			-30	
On-State Drain Current	$I_{D(on)}$	V_{DS}≦-10V,V_{GS}=-10V	-30			A
		V_{DS}≦-5V,V_{GS}=-4.5V	-5			
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V,I_D=-9.0A		11	17	mΩ
		V_{GS}=-4.5V,I_D=-7.0A		16	27	
Forward Transconductance	g_{FS}	V_{DS}=-10V,I_D=-10A		23		S
Diode Forward Voltage	V_{SD}	I_S=-2.3A,V_{GS}=0V		-0.7	-1.3	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-15V,V_{GS}=-4.5V I_D≡-10.0A		20	35	nC
Gate-Source Charge	Q_{gs}			6		
Gate-Drain Charge	Q_{gd}			10		
Input Capacitance	C_{iss}	V_{DS}=-15V,V_{GS}=0V f=1MHz		1960		pF
Output Capacitance	C_{oss}			380		
Reverse Transfer Capacitance	C_{rss}			325		
Turn-On Time	$t_{d(on)}$	V_{DD}=-15V,R_L=3Ω I_D≡-10.0A,V_{GEN}=-10V R_G=1Ω		10	25	ns
	t_r			15	30	
Turn-Off Time	$t_{d(off)}$			30	60	
	t_f			10	20	

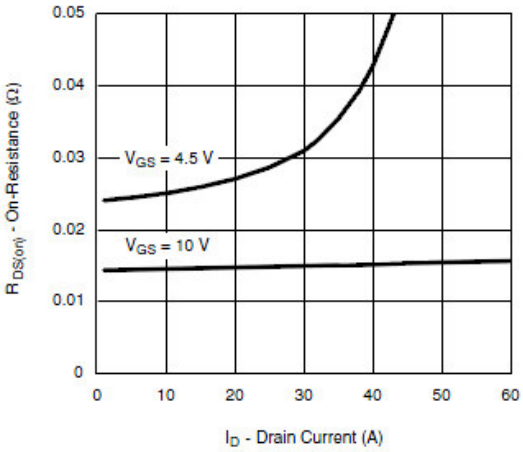
Typical Characteristics



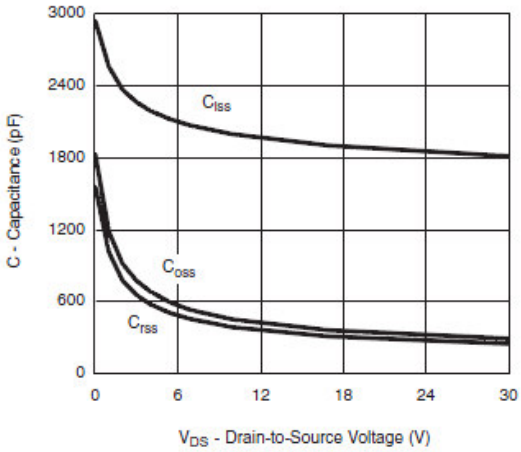
Output Characteristics



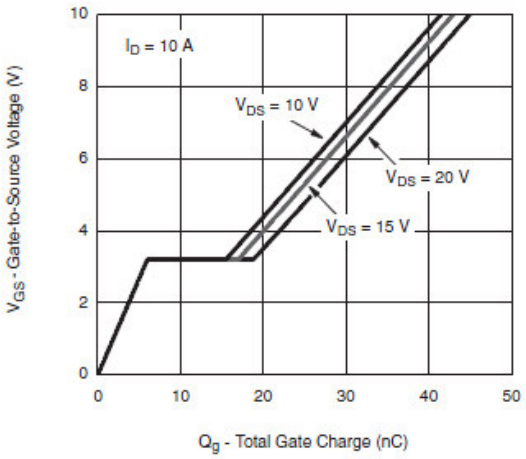
Transfer Characteristics



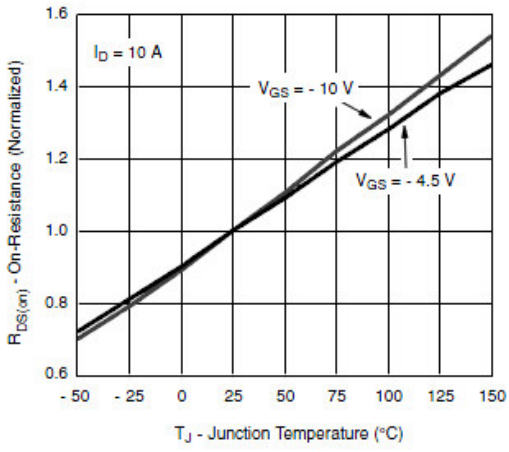
On-Resistance vs. Drain Current



Capacitance

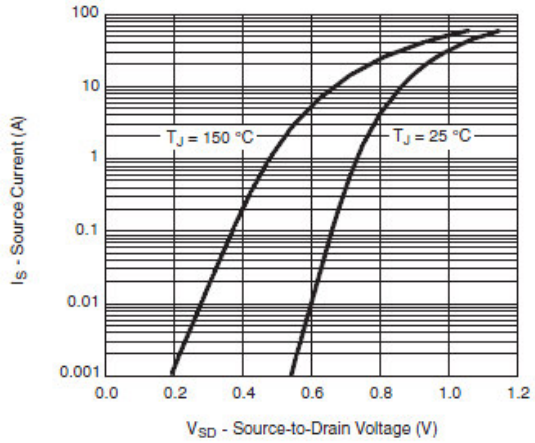


Gate Charge

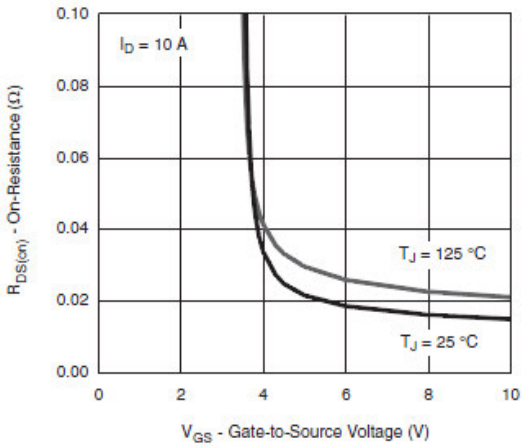


On-Resistance vs. Junction Temperature

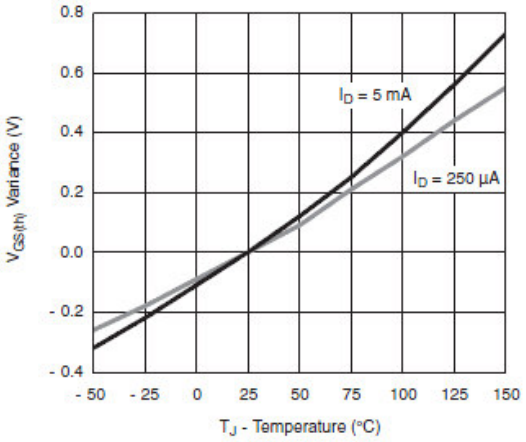
Typical Characteristics



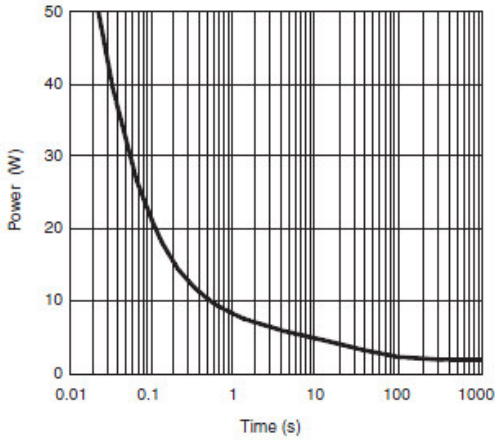
Source-Drain Diode Forward Voltage



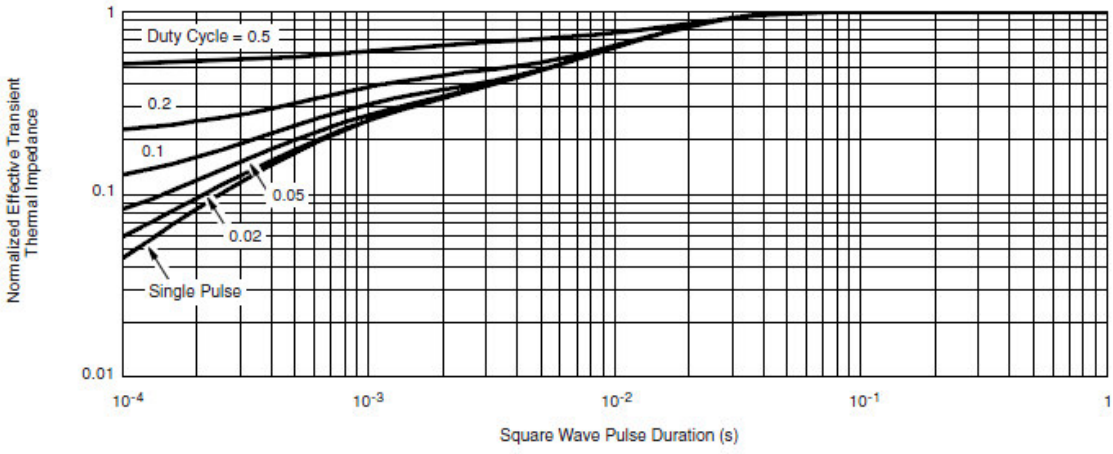
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



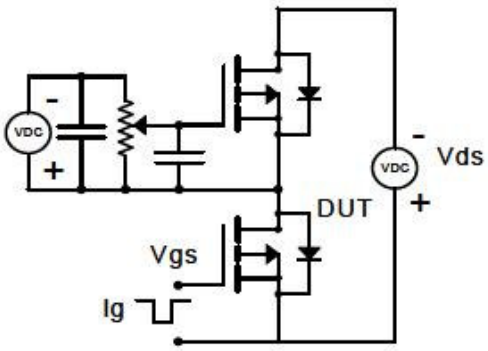
Single Pulse Power, Junction-to-Ambient

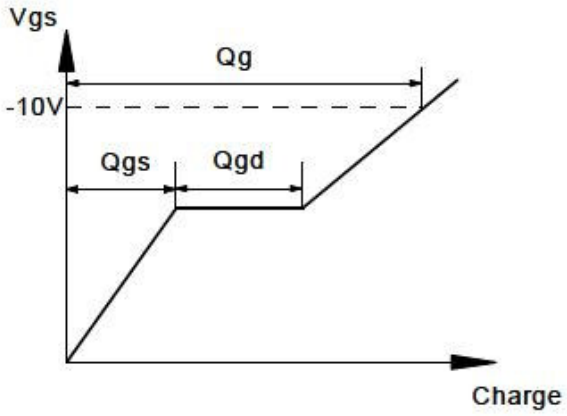


Normalized Thermal Transient Impedance, Junction-to-Case

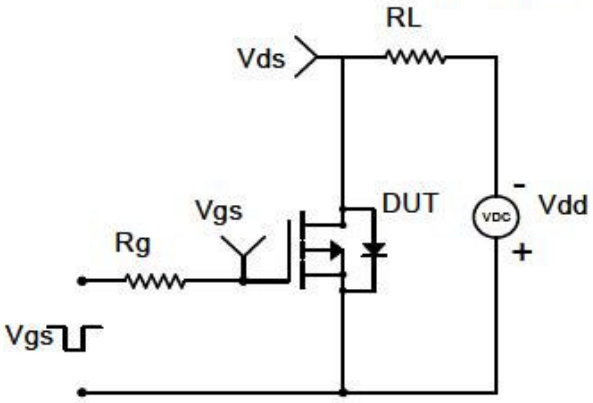
Typical Characteristics

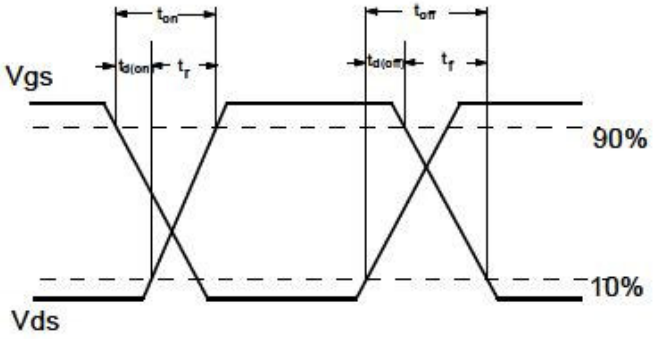
Gate Charge Test Circuit & Waveform



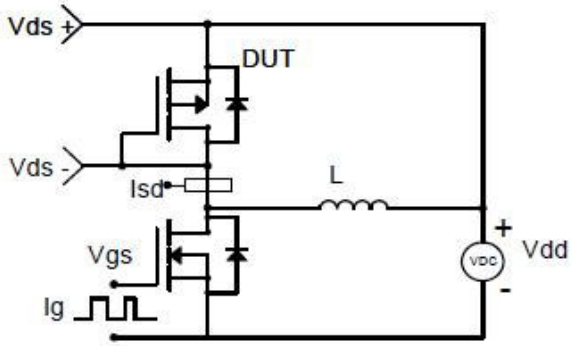


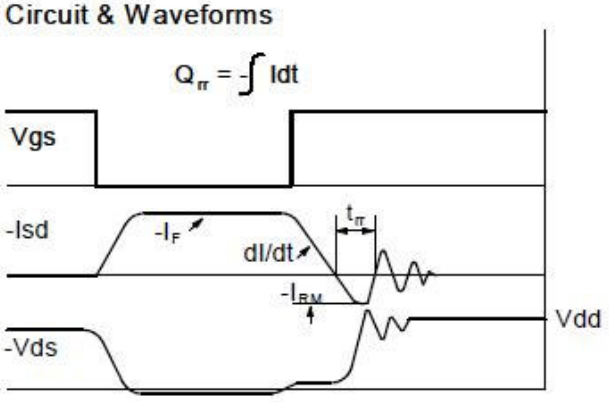
Resistive Switching Test Circuit & Waveforms



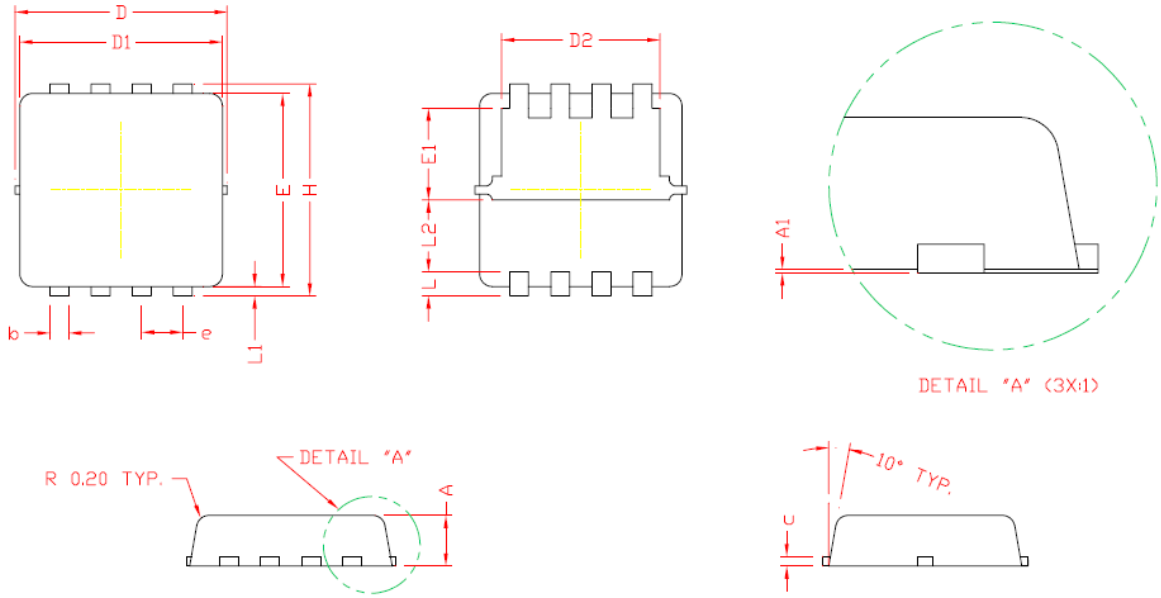


Diode Recovery Test Circuit & Waveforms





Package Information (DFN3.3X3.3-8L)



DIMENSIONS

REF.	Millimeters		REF.	Millimeters	
	Min.	Max.		Min.	Max.
A	0.70	0.90	E	3.00	3.20
A1	0.00	0.05	E1	1.35	1.55
b	0.24	0.35	e	0.65 BSC.	
c	0.10	0.20	H	3.20	3.40
D	3.25	3.40	L	0.30	0.50
D1	3.05	3.25	L1	0.10	0.20
D2	2.40	2.60	L2	1.13 Ref.	

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